

ABSTRACT

A semiconductor device of the present disclosure includes a substrate, a first semiconductor element disposed on the substrate, a first sealing layer sealing the first semiconductor element, and a second semiconductor element disposed to cover a surface in the first sealing layer opposite to the side of the substrate and having a larger area than an area of the first semiconductor element, the first sealing layer is composed of a cured product of a thermosetting resin composition, and a melt viscosity at 120°C of the thermosetting resin composition is 2500 to 11500 Pa·s.

Fig. 1